N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	145A
$R_{DS(ON)}$(at V_{GS}=10V)	3m
100% EAS Tested	
100% [illegible] V_{DS} Tested	
ESD Level (HBM)	Class 2

General Description

Split gate trench MOSFET technology

Low RDS(on) & FOM

Excellent stability and uniformity

Moisture Sensitivity Level 1

en-US

■Typical Electrical and Thermal Characteristics Diagrams

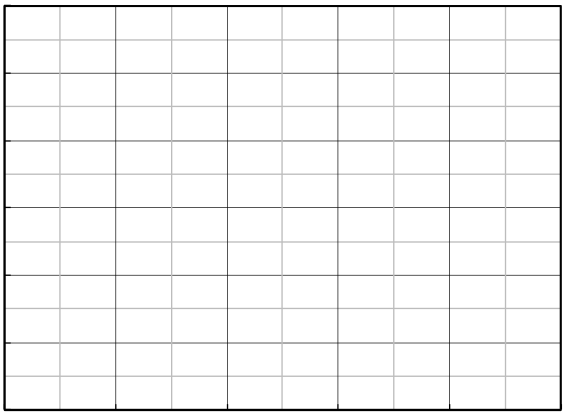


Figure 1. Output Characteristics; typical values

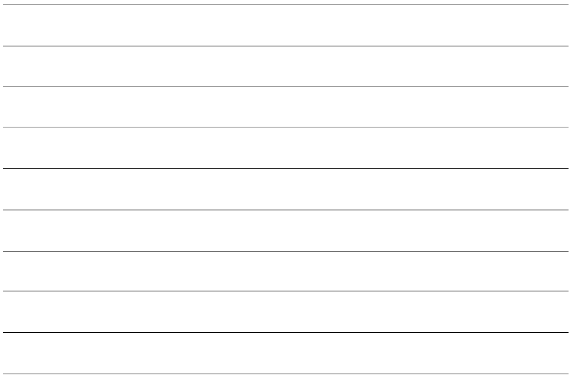


Figure 2. Transfer Characteristics; typical values

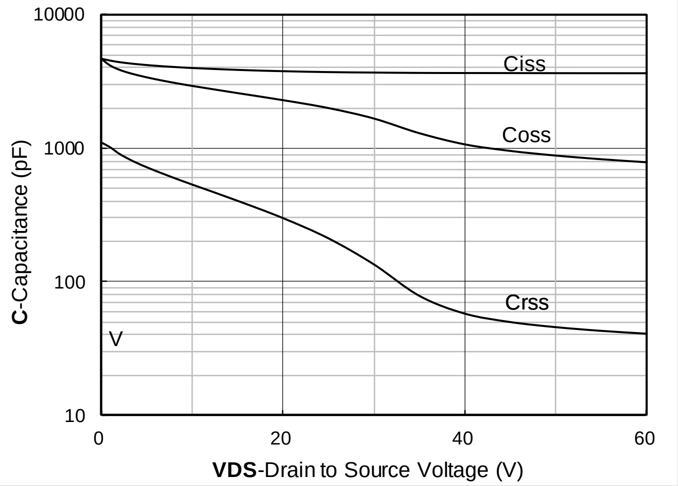


Figure 3. Capacitance Characteristics; typical values

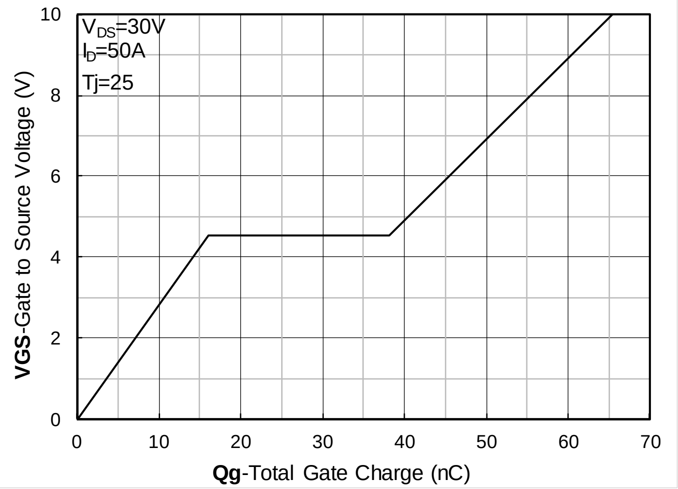


Figure 4. Gate Charge; typical values

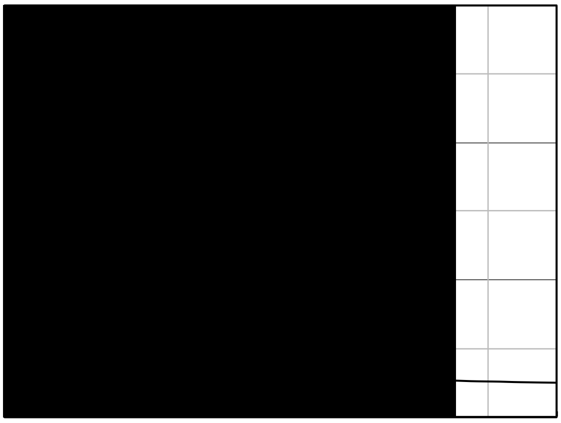


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

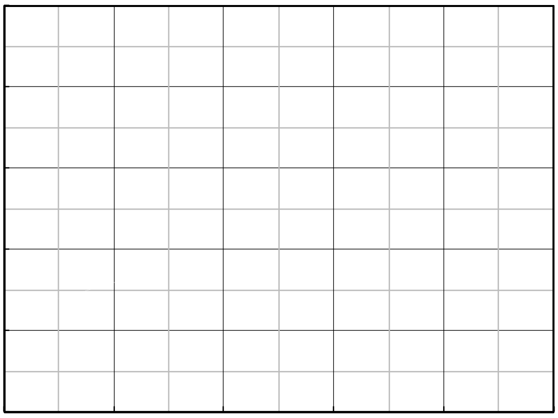


Figure 6. Normalized On-Resistance

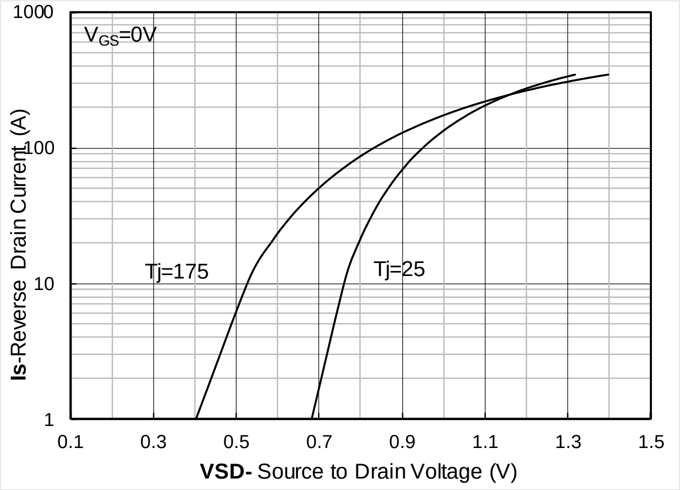


Figure 7. RDS(on) vs. Drain Current; typical values

Figure 8. Forward characteristics of reverse diode; typical values

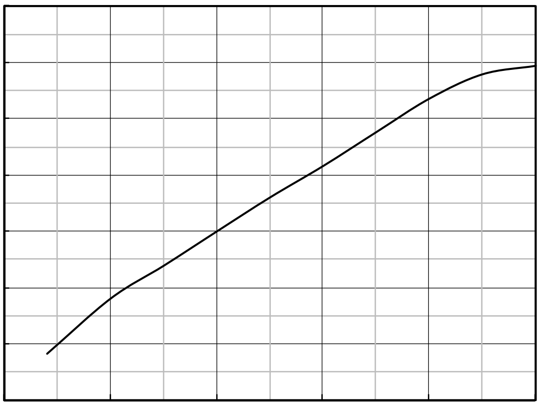
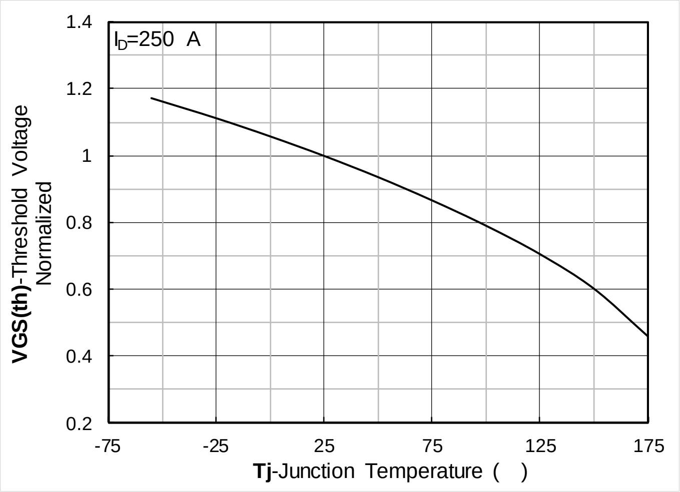


Figure 9. Normalized breakdown voltage



Figure

Test Circuits & Waveforms

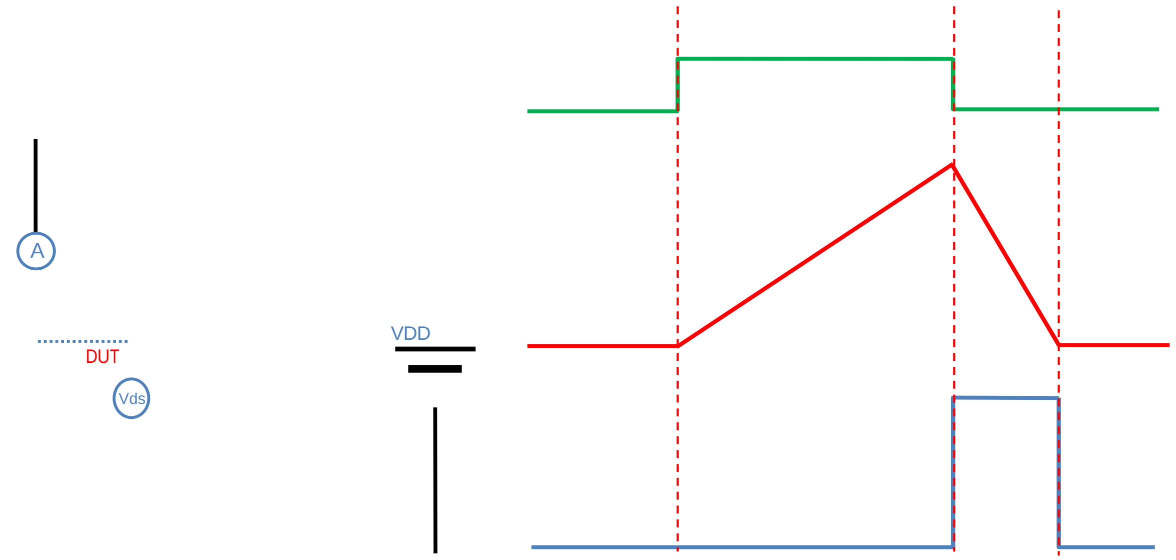


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

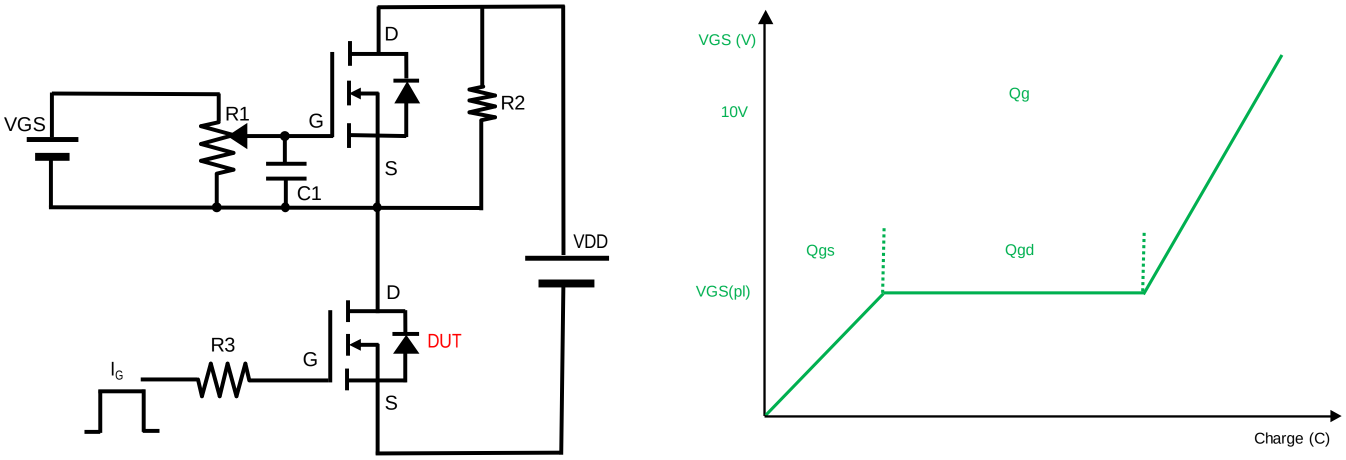


Figure B. Gate Charge Test Circuit & Waveform

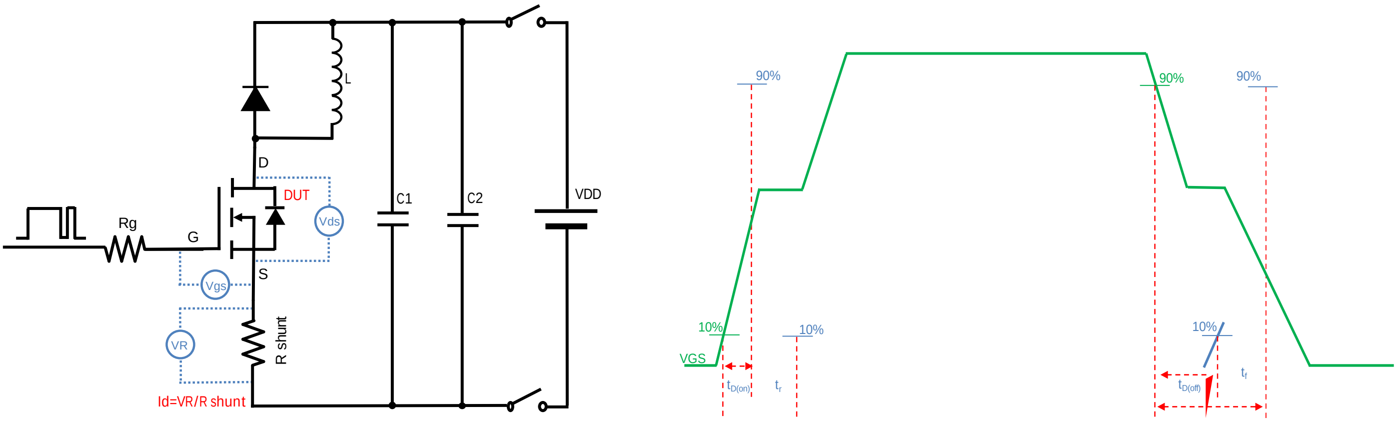


Figure C. Resistive Switching Test Circuit & Waveform

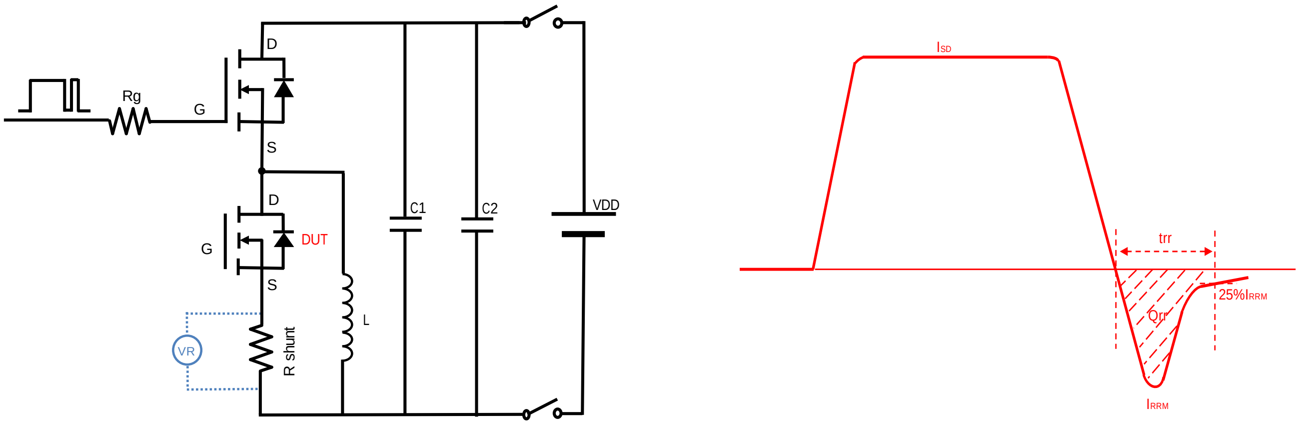


Figure D. Diode Recovery Test Circuit & Wav* nBT/F5 10.08 Tf1 0 0 1 357.41 595.54 Tm0 g

Marking Information

Note
1. All marking is at middle of the product body
2. All ma